

Preface

This volume is a collection of papers to be presented at the 10th International Autumn Meeting „Gettering and Defect Engineering in Semiconductor Technology – GADEST 2003,” which will take place from 21 – 26 September 2003 at the Seehotel Zeuthen, in the state of Brandenburg, Germany. The Seehotel Zeuthen, near Berlin, is an excellent place for a forum for interaction between scientists and engineers engaged in the field of semiconductor defect physics, materials science and technology; and, to reflection on future aspects in the conversion era from the microelectronics to the nanoelectronics. Furthermore a special ambition is to strengthen the interaction and exchange between the communities working in the fields of crystalline silicon for electronics and photovoltaics.

The International Autumn Meeting of GADEST is held bi-annually and has a long tradition that began in 1985, with the conference at Garzau, East Germany. The main purpose was to hold an informal gathering between Eastern and Western researchers in the field of defect engineering and gettering. Recent events were organized in Garzau (1987, 1989), Klingemühle (1991, 1993) and Wulkow (1995) (also in Germany) and following in Spa, Belgium (1997), Höör, Sweden (1999) and Catania, Italy (2001). The 10th GADEST will be held near the same place where the first meeting was held.

The present proceedings contain 20 invited and 76 contributed (oral and poster presentations) papers from over 90 research institutions and from more than 20 different countries. The invited papers, presented by internationally recognised experts in the field, review the state-of-the-art and future trends in their respective research field. The symposium and (its proceeding volume) are organized in 11 sessions:

1. Advanced Silicon Material
2. Oxygen, Nitrogen and Hydrogen Related Phenomena
3. Crystalline Silicon for Solar Cells
4. Silicon Germanium on Silicon
5. Extended Defects in Silicon and Influence on Luminescence
6. Implantation Related Phenomena
7. Point Defects, Impurities, and Deep Levels
8. Dislocations in Semiconductors
9. Diagnostics, Characterization Techniques
10. Gettering
11. Future Aspects

A meeting like this can never be organized without the help and support of a skilled team. We gratefully acknowledge the help of all members of the Executive Committee and the International Program Committee in setting up the conference.

The editors wish to thank the members of International Program Committee for selecting the invited and the contributed paper. We wish to thank the authors for their timely submission of manuscripts which made these proceedings possible. We also want to thank Mrs. I. Staar (IHP/BTU Joint Lab, Cottbus), whose assistance in editing the finalized version was very helpful. Last, but not least, we are greatly indebted to our sponsors. Without their help, we would not have been able to organize the conference.

We hope to see you again at the 11th International Autumn Meeting, which will be held in 2005.

Frankfurt (Oder), July 2003

Hans Richter

Martin Kittler

